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Quarterly Reliability Monitoring Results

Quarters: Q1/2022 to Q4/2023

Based on structural similarity

Supplier		User Part Number						
Nexperia B.V.		PMEG6020ER						
Name of Laboratory Assembly reliability labs		Part Description						
		Nexperia DHAM	Schottky					
		SMD package						
Test		Test Conditions	Duration	# Lots	# Quantity	# Rejects		
	TEST							
	Pre- and Post-Stress							
# 1	Electrical Test	Tamb = 25 °C	N/A	see below	all parts	see below		
		JESD22-A113						
		Bake Tamb = 125 °C	24 hours					
	PC	Soak Tamb = 85 °C, RH = 85%	168 hours					
# 2	Preconditioning	Reflow soldering	3 cycles	1514	64430	0		
		MIL-STD-750-1						
	HTRB	M1038 Method A Tj = Tjmax, Vr = 100% of max. datasheet						
	High Temperature Reverse	reverse voltage ^[1]						
# 5	Bias	reverse voltage	1000 hours	206	9320	0		
	тс							
# 7	Temperature Cycling	JESD22-A104 -65 °C to Timax, not to exceed 150°C		211	14000	0		
# /	remperature cycling		500 cycles	311	14080	0		
	UHAST	JESD22-A118						
# 8 or # 8a	Unbiased HAST	Tamb = 130 °C, RH = 85 %	– 96 hours	311	14080	0		
		JESD22-A102						
	AC	Tamb = $121 ^{\circ}$ C, RH = $100 ^{\circ}$						
	Autoclave	Pressure = $205 \text{ kPa} (29.7 \text{ psia})$						
# 0a								
	H3TRB	JESD22-A101						
	High Humidity High	Tamb = $85 ^{\circ}$ C, RH = 85% , VR = 80% of						
# 9	Temperature Reverse Bias	rated reverse voltage ^{[1], [2]}	1000 hours	311	14080	0		
π J	· ·	MIL-STD-750 Method 1037				-		
	IOL	ton = toff, devices powered to insure ΔTj =						
# 10	Intermittent Operating Life		333 hours	312	14120	0		
						-		
	RSH	JESD22-A111						
# 20	Resistance to Solder Heat	260 °C ± 5 °C	10 s	269	8070	0		
	SD							
# 21	Solderability	J-STD-002		222	6660	0		

[1] The physical limitations of Schottky diodes have to be considered (thermal runaway).

[2] The maximum applied voltage is limited by test chamber set up and does not exceed 115V.

Calculation of FIT and MTTF

Test considered for FIT calculation: High Temperature Reverse Bias (HTRB, Test # 5) Confidence level 60%, derated to 55 °C, activation energy 0.7 eV, test time 168 to 1000 hours

Wafer Fab T	Technology	Quantity	Rejects	Failure Rate (FIT)	MTTF (hrs)
Nexperia					
DHAM S	Schottky	9320	0	0,46	2,19E+09

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